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MARKING

3.3V ECL Phase-Frequency Detector

MC100EP140

Description

The MC100EP140 is a three state phase frequency-detector intended for phase-locked loop applications which require a minimum amount of phase and frequency difference at lock. Since the part is designed with fully differential internal gates, the noise is reduced throughout the circuit, especially at high speeds. The basic operation of a Phase/Frequency Detector (PFD) is to "compare" an incoming signal (feedback) to a set reference signal. When the Reference (R) and Feedback (FB) inputs are unequal in frequency and/or phase, the differential UP (U) and DOWN (D) outputs will provide pulse streams which, when subtracted and integrated, provide an error voltage for control of a VCO. Detector states of operation are shown in the Figure 2 and the State Table.

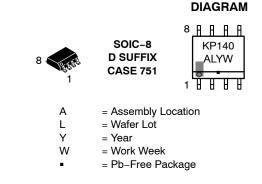
The typical output amplitude of the EP140 is 400 mV, allowing faster switching time and greater bandwidth. For proper operation, the input edge rate of the R and FB inputs should be less than 5 ns.

More information on Phase Lock Loop operation and application can be found in AND8040.

The pinout is shown in Figure 1, the logic diagram in Figure 3, and the typical termination in Figure 5.

Features

- 500 ps Typical Propagation Delay
- Maximum Frequency > 2.1 GHz Typical
- Fully Differential Internally
- Advanced High Band Output Swing of 400 mV
- Transfer Gain: 1.0 mV/Degree at 1.4 GHz 1.2 mV/Degree at 1.0 GHz
- Rise and Fall Time: 100 ps Typical
- The 100 Series Contains Temperature Compensation
- PECL Mode Operating Range: V_{CC} = 3.0 V to 3.6 V with V_{EE} = 0 V
- NECL Mode Operating Range: $V_{CC} = 0 V$ with $V_{EE} = -3.0 V$ to -3.6 V
- Open Input Default State
- These are Pb–Free Devices



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MC100EP140

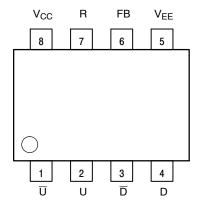


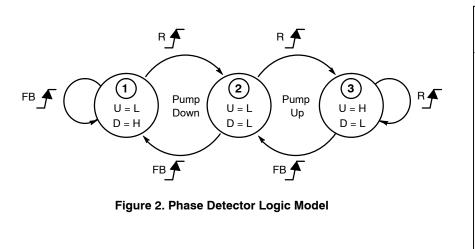
Figure 1. 8-Lead Pinout (Top View)

Table 1. PIN DESCRIPTION

PIN	FUNCTION			
D, D	Differential Down Outputs			
U, U	Differential Up Outputs			
R*	ECL Reference Input			
FB*	ECL Feedback Input			
V _{CC}	Positive Supply			
V _{EE}	Negative Supply			

* Pins will default LOW when left open.

Table 2. STATE TABLE



PHASE DETECTOR	INF	νUT	Ουτρυτ		
STATE	R	FB	U	D	
PUMP DOWN 2-1-2					
2	L	L	L	L	
2–1	L	Н	L	н	
1–2	Н	L	L	L	
2	L	L	L	L	
PUMP UP 2-3-2					
2	L	L	L	L	
2–3	н	L	н	L	
3–2	Н	н	L	L	
2	L	L	L	L	

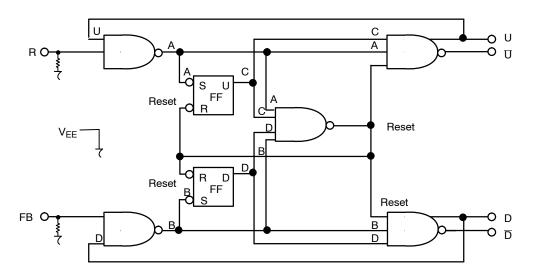


Figure 3. Logic Diagram

Table 3. ATTRIBUTES

Characterist	Value						
Internal Input Pulldown Resistor	75 kΩ						
Internal Input Pullup Resistor		37.5 kΩ					
ESD Protection	> 2 kV > 200 V > 2 kV						
Moisture Sensitivity, Indefinite Time	Out of Drypack (Note 1)	Pb Pkg	Pb-Free Pkg				
	SOIC-8	Level 1	Level 1				
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in					
Transistor Count	457 Devices						
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test							

1. For additional information, see Application Note AND8003/D.

Table 4. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		6	V
V_{EE}	NECL Mode Power Supply	V _{CC} = 0 V		-6	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$\begin{array}{l} V_{I} \leq V_{CC} \\ V_{I} \geq V_{EE} \end{array}$	6 -6	V V
l _{out}	Output Current	Continuous Surge		50 100	mA mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 SOIC-8	190 130	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8	41 to 44	°C/W
T _{sol}	Wave Solder Pb Pb-Free			265 265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 5. 100EP DC CHARACTERISTICS, PECL V_{CC} = 3.3 V, V_{EE} = 0 V (Note 2)

		-40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	45	65	85	50	70	90	53	73	93	mA
V _{OH}	Output HIGH Voltage (Note 3)	2255	2350	2475	2275	2400	2525	2300	2425	2550	mV
V _{OL}	Output LOW Voltage (Note 3)	1755	1900	2025	1800	1925	2050	1825	1950	2075	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
VIL	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. 2. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.3 V to -0.3 V. 3. All loading with 50 Ω to V_{CC} - 2.0 V.

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Table 6. 100EP DC CHARACTERISTICS, NECL V_{CC} = 0 V, V_{EE} = -3.6 V to -3.0 V (Note 4)

		-40°C			25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	45	65	85	50	70	90	53	73	93	mA
V _{OH}	Output HIGH Voltage (Note 5)	-1075	-950	-825	-1025	-900	-775	-1000	-875	-750	mV
V _{OL}	Output LOW Voltage (Note 5)	-1525	-1400	-1275	-1500	-1375	-1250	-1475	-1350	-1225	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1225		-880	-1225		-880	-1225		-880	mV
V _{IL}	Input LOW Voltage (Single-Ended)	-1945		-1625	-1945		-1625	-1945		-1625	mV
I _{IH}	Input HIGH Current			150			150			150	μΑ
IIL	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

4. Input and output parameters vary 1:1 with V_{CC}. 5. All loading with 50 Ω to V_{CC} – 2.0 V.

			-40°C			25°C						
Symbol	Characteristic		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Frequency (Figure 4)			> 2			> 2			> 2		GHz
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential	R to U, FB to D FB to U, R to D	300 400	450 600	6002 800	325 450	475 650	625 850	350 500	500 700	650 900	ps
t _{JITTER}	Cycle-to-Cycle Jitter (Figure 4)			.2	< 1		.2	< 1		.2	< 1	ps
V _{PP}	Input Voltage Swing		400	800	1200	400	800	1200	400	800	1200	mV
t _r t _f	Output Rise/Fall Times (20% - 80%)	Q, <u>Q</u>	50	90	180	60	100	200	70	120	220	ps

Table 7. AC CHARACTERISTICS V_{CC} = 0 V; V_{EE} = -3.0 V to -3.6 V or V_{CC} = 3.0 V to 3.6 V; V_{EE} = 0 V (Note 6)

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

6. Measured using a 750 mV V_{PP} pk-pk, 50% duty cycle, clock source. All loading with 50 Ω to V_{CC} – 2.0 V.

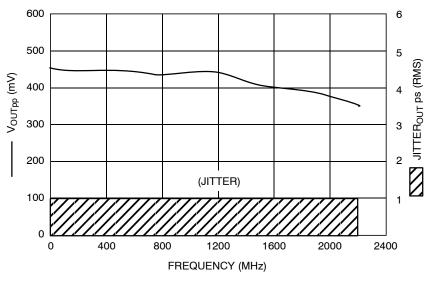


Figure 4. F_{max}/Jitter

MC100EP140

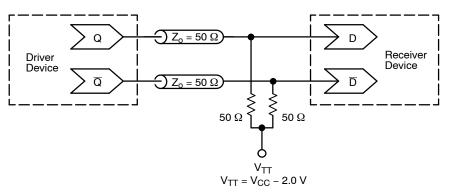


Figure 5. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020/D – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100EP140DG	SOIC–8 (Pb–Free)	98 Units / Rail
MC100EP140DR2G	SOIC–8 (Pb–Free)	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D	-	ECL Clock Distribution Techniques
AN1406/D	-	Designing with PECL (ECL at +5.0 V)
AN1503/D	-	ECLinPS [™] I/O SPiCE Modeling Kit
AN1504/D	-	Metastability and the ECLinPS Family
AN1568/D	-	Interfacing Between LVDS and ECL
AN1672/D	-	The ECL Translator Guide
AND8001/D	-	Odd Number Counters Design
AND8002/D	-	Marking and Date Codes
AND8020/D	-	Termination of ECL Logic Devices
AND8066/D	-	Interfacing with ECLinPS
AND8090/D	-	AC Characteristics of ECL Devices

ECLinPS is a trademark of Semiconductor Components Industries, LLC (SCILLC).

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

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8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

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STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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